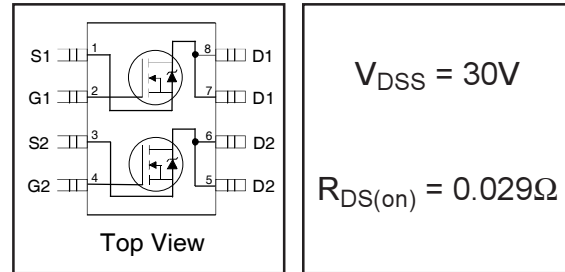


IRF7313PbF

HEXFET® Power MOSFET

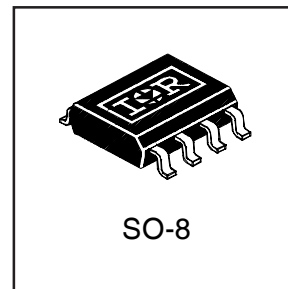
- Generation V Technology
- Ultra Low On-Resistance
- Dual N-Channel MOSFET
- Surface Mount
- Fully Avalanche Rated
- Lead-Free



Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques.



Absolute Maximum Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)

	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^①	I_D	$T_A = 25^\circ C$	A
		$T_A = 70^\circ C$	
Pulsed Drain Current	I_{DM}	30	
Continuous Source Current (Diode Conduction)	I_S	2.5	
Maximum Power Dissipation ^②	P_D	$T_A = 25^\circ C$	W
		$T_A = 70^\circ C$	
Single Pulse Avalanche Energy ^②	E_{AS}	82	mJ
Avalanche Current	I_{AR}	4.0	A
Repetitive Avalanche Energy	E_{AR}	0.20	mJ
Peak Diode Recovery dv/dt ^③	dv/dt	5.8	V/ ns
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to + 150	$^\circ C$

Thermal Resistance Ratings

Parameter	Symbol	Limit	Units
Maximum Junction-to-Ambient ^④	$R_{\theta JA}$	62.5	$^\circ C/W$

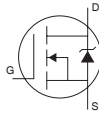
IRF7313PbF

International
IR Rectifier

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.022	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	0.023	0.029	Ω	V _{GS} = 10V, I _D = 5.8A ④
		—	0.032	0.046		V _{GS} = 4.5V, I _D = 4.7A ④
V _{GS(th)}	Gate Threshold Voltage	1.0	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	—	14	—	S	V _{DS} = 15V, I _D = 5.8A
I _{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V _{DS} = 24V, V _{GS} = 0V
		—	—	25		V _{DS} = 24V, V _{GS} = 0V, T _J = 55°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	22	33	nC	I _D = 5.8A
Q _{gs}	Gate-to-Source Charge	—	2.6	3.9		V _{DS} = 15V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	6.4	9.6		V _{GS} = 10V, See Fig. 10 ④
t _{d(on)}	Turn-On Delay Time	—	8.1	12	ns	V _{DD} = 15V
t _r	Rise Time	—	8.9	13		I _D = 1.0A
t _{d(off)}	Turn-Off Delay Time	—	26	39		R _G = 6.0Ω
t _f	Fall Time	—	17	26		R _D = 15Ω ④
C _{iss}	Input Capacitance	—	650	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	320	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	130	—		f = 1.0MHz, See Fig. 9

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	30		
V _{SD}	Diode Forward Voltage	—	0.78	1.0	V	T _J = 25°C, I _S = 1.7A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	45	68	ns	T _J = 25°C, I _F = 1.7A
Q _{rr}	Reverse Recovery Charge	—	58	87	nC	di/dt = 100A/μs ③

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting T_J = 25°C, L = 10mH
R_G = 25Ω, I_{AS} = 4.0A.
- ③ I_{SD} ≤ 4.0A, di/dt ≤ 74A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 150°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Surface mounted on FR-4 board, t ≤ 10sec.

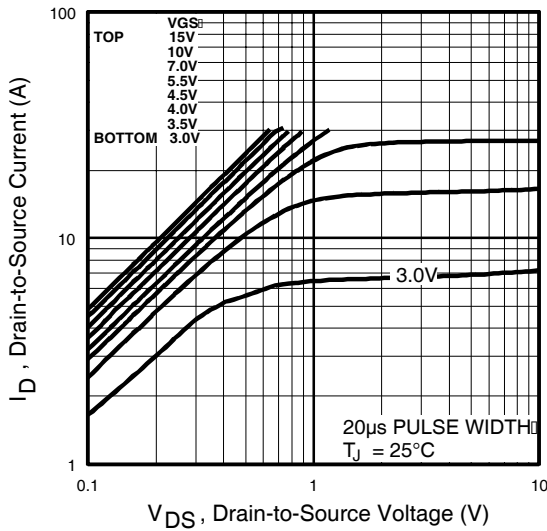


Fig 1. Typical Output Characteristics

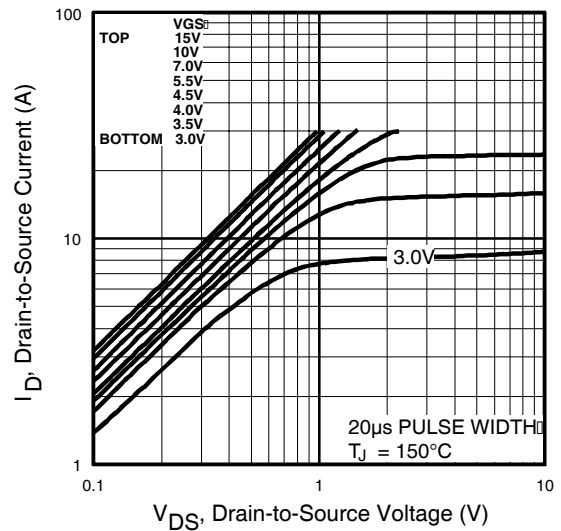


Fig 2. Typical Output Characteristics

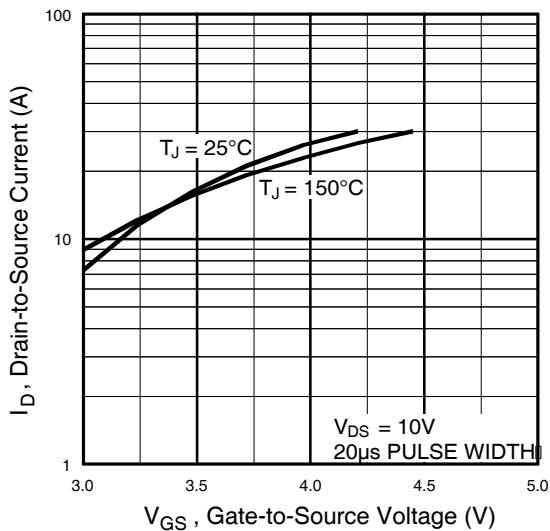


Fig 3. Typical Transfer Characteristics

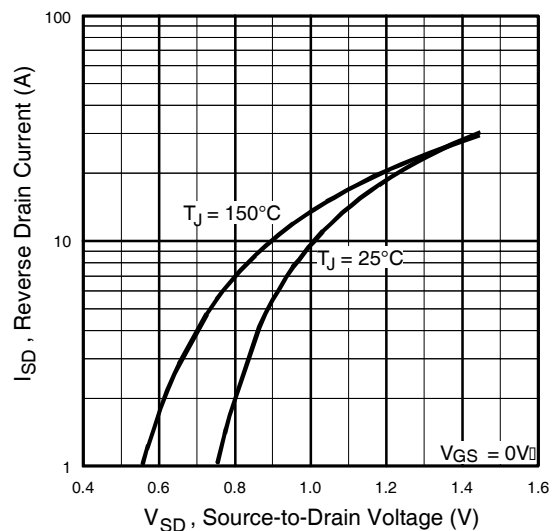


Fig 4. Typical Source-Drain Diode Forward Voltage

VDS

IRF7313PbF

International
IR Rectifier

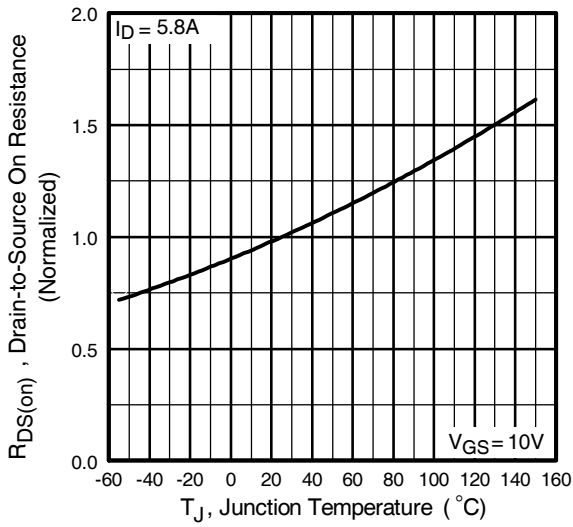


Fig 5. Normalized On-Resistance Vs. Temperature

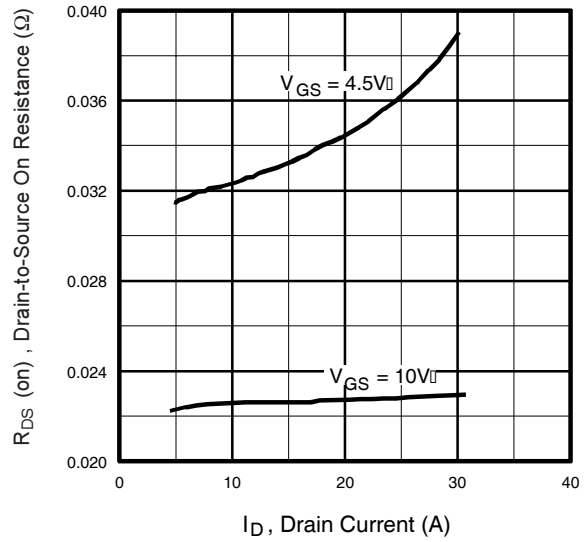


Fig 6. Typical On-Resistance Vs. Drain Current

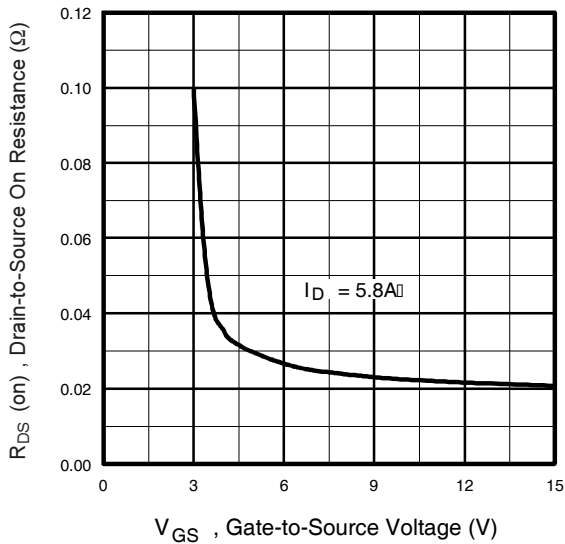


Fig 7. Typical On-Resistance Vs. Gate Voltage

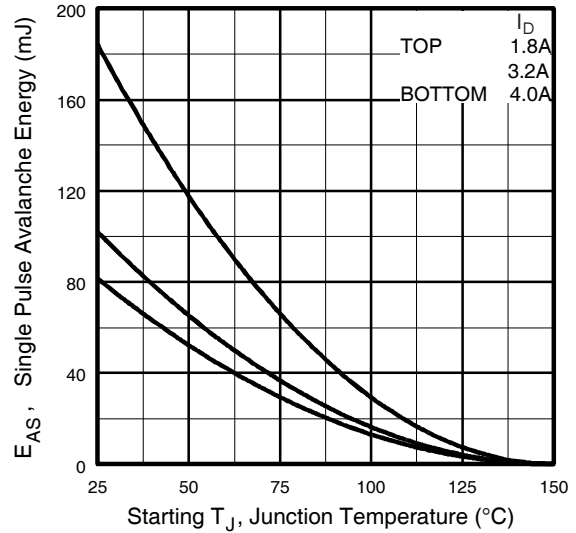


Fig 8. Maximum Avalanche Energy Vs. Drain Current

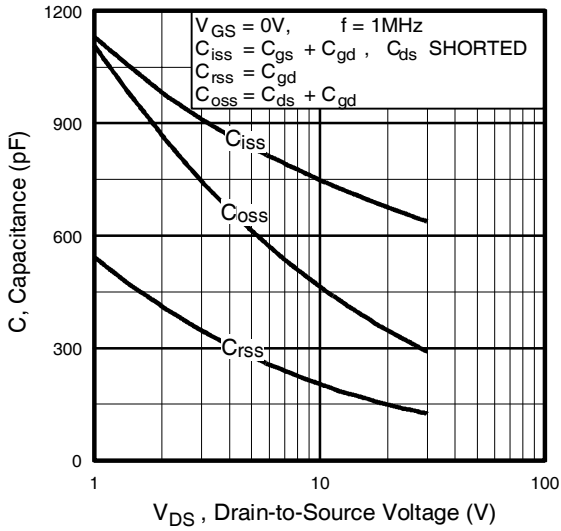


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

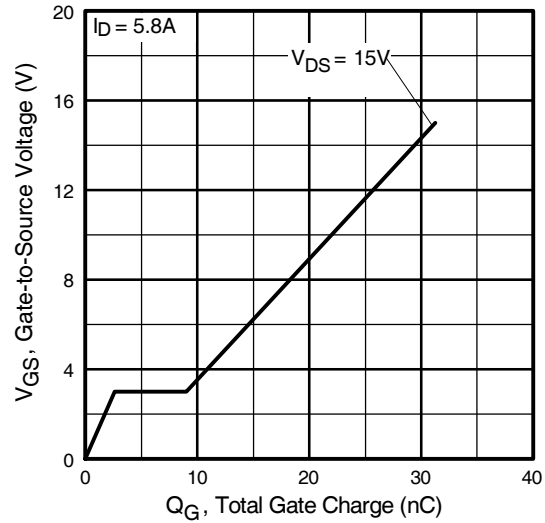


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

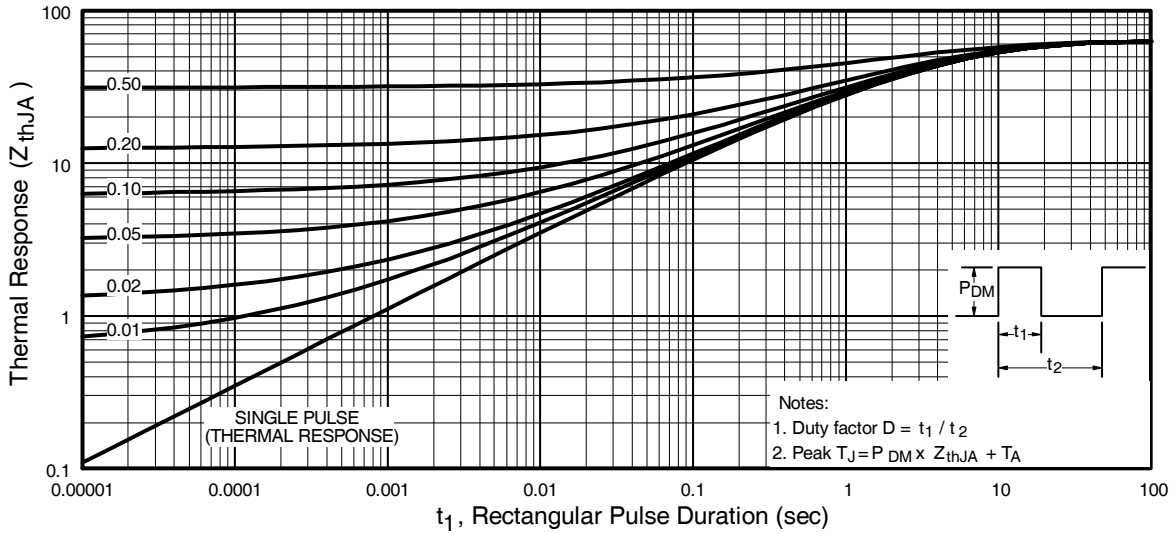
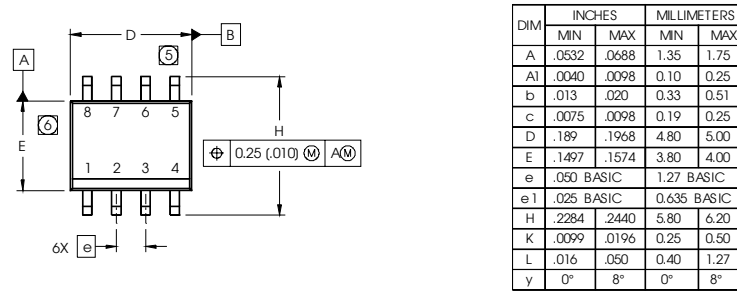


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

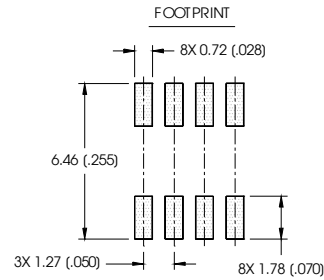
IRF7313PbF

SO-8 Package Outline

Dimensions are shown in millimeters (inches)

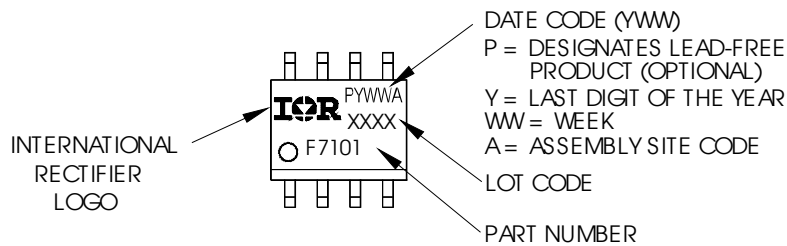


- NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: MILLIMETER
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA
 5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
 6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
 7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



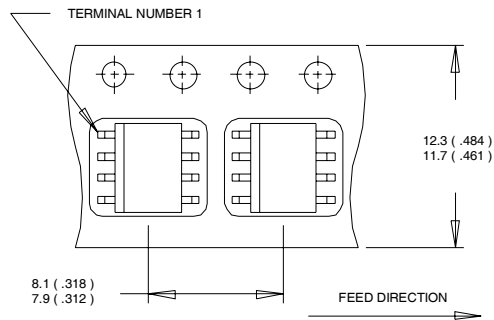
SO-8 Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



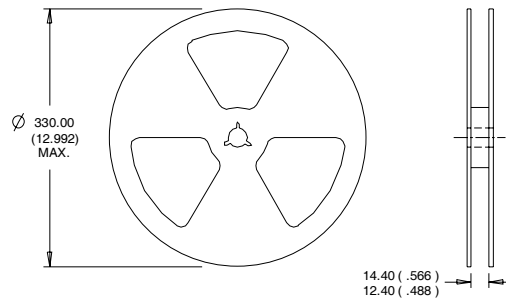
SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Consumer market.
 Qualifications Standards can be found on IR's Web site.

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies office (www.infineon.com).

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon\(英飞凌\)](#)